

NEW!

Picosecond Gain Switched Laser "ANGIS"



Wavelength	1064 nm / 532 nm / 355 nm
Pulse duration	< 50 ps
Energy	>100 μ J
Repetition rate	single shot up to 10 kHz
Beam profile	Gaussian, M2 <1.2
Spectrum	SLM

Scientific Applications

- Remote Laser Sensing
- Time resolved fluorescence spectroscopy
- Laser induced acoustic wave generation
- OPO pumping
- Other spectroscopic applications

Industrial Applications

- Microprocessing of Dielectric Wafers, Silicon Wafers, Flexible Printed
- Circuit Boards (FPCB), Printed Circuit Boards (PCB)
- Flat Panel Display, LCD/LED/OLED Repair

Features

- Ultra-compact, integrated driver
- Air cooled
- Passively or Actively Q-switched 880 nm Pump Laser
- No Semiconductor Modulator (SESAM), No Mode Locking
- Cost-effective

“ANGIS” Picosecond Industrial Laser

Pulse energy	
1064 nm	>100 µJ
532 nm	>50 µJ
355 nm	>30 µJ
Pulse duration	<50 ps
Energy stability (RMS)	
1064 nm	<1.0 %
532 nm	<2.0 %
355 nm	<3.0 %
Power drift	±1.0 %
Pulse repetition rate	Single shot - 10 kHz
Beam profile	Gaussian
Output beam diameter	
1064 nm	2.5±0.5 mm
M ²	<1.2
Polarization	linear, horizontal at 1064 nm
Spectral linewidth	SLM
Beam pointing stability	<10 urad
Optical jitter	<100 ns
Dimensions	390x250x164 mm
Environmental operational conditions	Indoor use only
Cooling	Air cooled
Ambient temperature	17-30 °C
Relative humidity	10-65 %
Power	
Mains voltage	100-230 VAC, single phase, 50-60 Hz
Power consumption	600 W typ